

Silicon Diode

BY202/2

200V / 1,5A

DATASHEET

OEM – Telefunken

Source: Telefunken Databook 1977

BY 202/...**Silizium-Mesa-Dioden**
Silicon Mesa diodes

Anwendungen: Schneller Gleichrichter und Schalter z. B. für zeilenfrequenten Betrieb im Fernsehgerät und Schaltnetzteile.

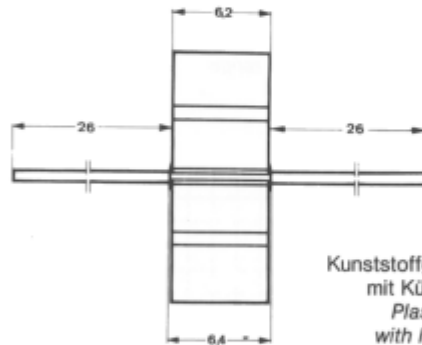
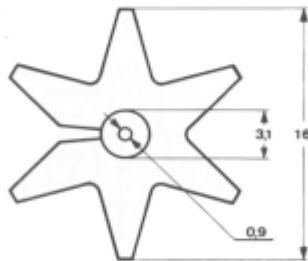
Applications: Fast rectifier and switch for example for TV-line output circuits and switch mode power supply.

Wesentliche Merkmale:

- Hohe Sperrspannung
- Kurze Schaltzeit
- Geringe Umschaltverluste

Features:

- High reverse voltage
- Short switching time
- Low switching loss

Abmessungen in mm
Dimensions in mm

Kunststoffgehäuse
mit Kühlkörper
Plastic case
with heat sink
Gewicht - Weight
max. 4,5 g

Typenbezeichnung = Kathodenanschluß
Type designation = Cathode terminal

Absolute Grenzdaten
Absolute maximum ratings

Periodische Spitzensperrspannung
Repetitive peak reverse voltage
 $f \leq 20 \text{ kHz}$, $t \leq 12 \mu\text{s}$

BY 202/2	U_{RRM}	250	V
BY 202/3	U_{RRM}	350	V
BY 202/4	U_{RRM}	450	V
BY 202/5	U_{RRM}	550	V
BY 202/6	U_{RRM}	650	V

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Sperrspannung, Scheitelsperrspannung
 Reverse voltage, crest working reverse voltage
 Fig. 1

$U_R = U_{RWM}$	200	V
$U_R = U_{RWM}$	300	V
$U_R = U_{RWM}$	400	V
$U_R = U_{RWM}$	500	V
$U_R = U_{RWM}$	600	V

Durchlaßstrom, Mittelwert
 Average forward current
 Fig. 3 bei U_R

$$R_{thJA} \leq 50^\circ\text{C/W}$$

I_{FAV}	1,5	A
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Periodischer Durchlaßspitzenstrom
 Repetitive peak forward current

I_{FRM}	10	A
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Stoßdurchlaßstrom
 Surge forward current
 $t_p \leq 10 \text{ ms}$

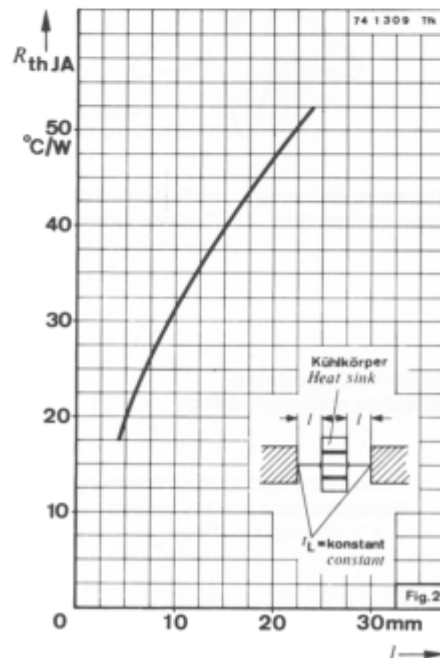
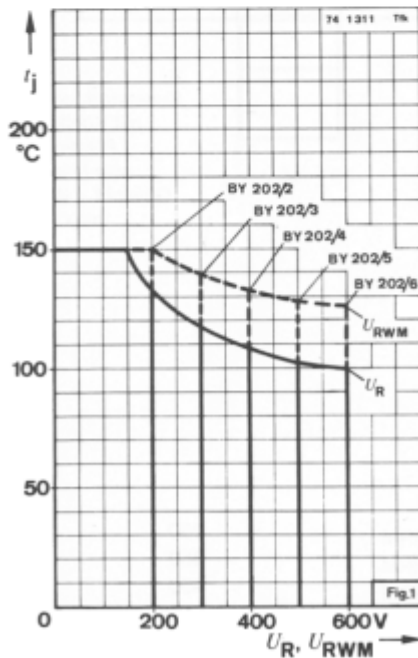
I_{FSM}	40	A
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Sperrschichttemperatur
 Junction temperature

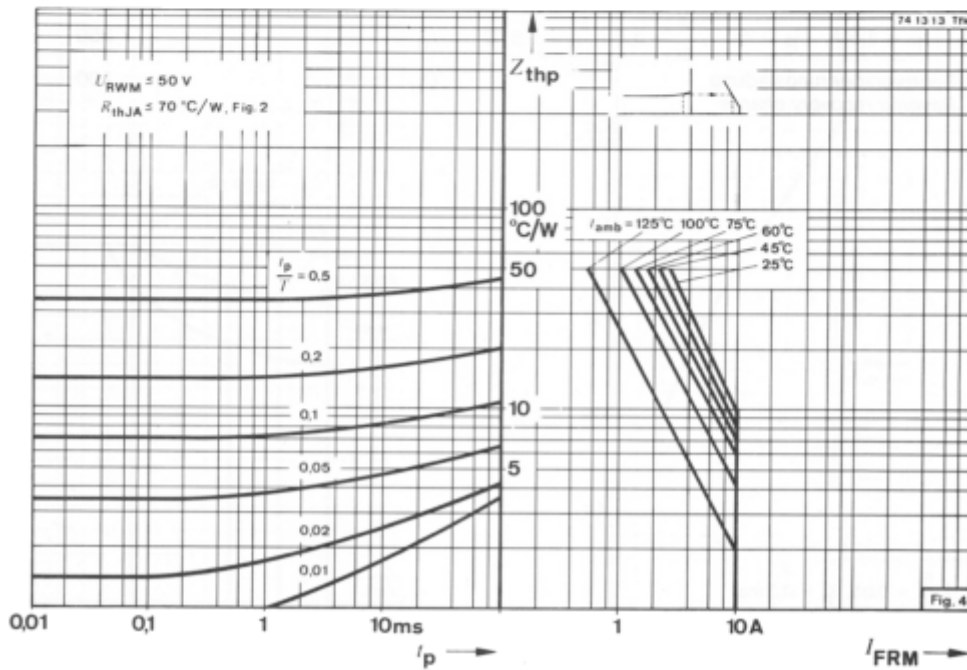
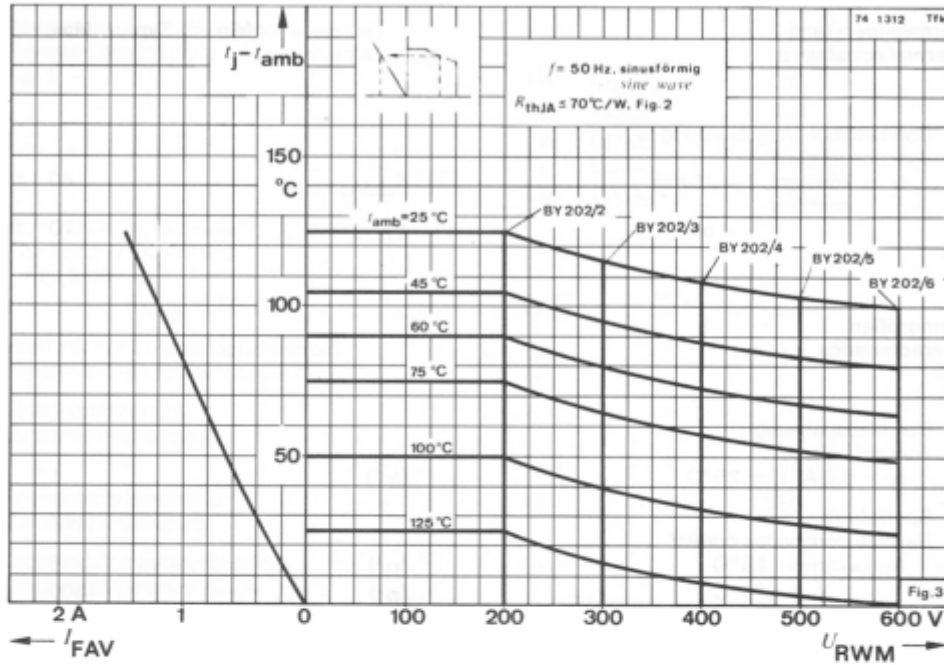
t_j	150	°C
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Lagerungstemperaturbereich
 Storage temperature range

t_{stg}	-40...+125	°C
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